

FDU6N25 N-Channel UniFETTM MOSFET 250 V, 4.4 A, 1.1 Ω

Features

- $R_{DS(on)}$ = 0.9 Ω (Typ.) @ V_{GS} = 10 V, I_D = 2.2 A
- Low Gate Charge (Typ. 4.5 nC)
- Low C_{rss} (Typ. 5 pF)
- 100% Avalanche Tested

Applications

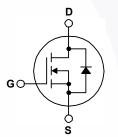
- LCD/LED/PDP TV
- Consumer Appliances
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

November 2013

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDU6N25	Unit
V _{DSS}	Drain-Source Voltage	Drain-Source Voltage		V
ID	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	4.4 2.6	A A
I _{DM}	Drain Current	- Pulsed (Note	1) 18	А
V _{GSS}	Gate-Source voltage	±30	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		2) 12	mJ
I _{AR}	Avalanche Current (Note 1)		1) 4.4	Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		1) 5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		3) 4.5	V/ns
P _D	Power Dissipation	(T _C = 25°C) - Derate Above 25°C	50 0.4	W W/°C
$T_{J,} T_{STG}$	Operating and Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FDU6N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	110	°C/W

Part Number		er Top Mark Pad		Packing Method	Reel Size	Ta	be Width	Qu	antity
FDU			IPAK	PAK Tube N/A		N/A		70 units	
Electric	al Char	acteristics T _c = 25°C	unless otherwi	ise noted.					
Symbol		Parameter		Conditions		Min.	Тур.	Max.	Unit
Off Charac	teristics								
BV _{DSS}	Drain-Sou	rce Breakdown Voltage	V _{GS} =	V _{GS} = 0 V, I _D = 250 μA		250			V
ΔBV_{DSS} / ΔT_{J}	Breakdow Coefficient	n Voltage Temperature	I _D = 2	I_D = 250 µA, Referenced to 25°C			0.25		V/∘C
I _{DSS}	Zero Gate Voltage Drain Current			$V_{DS} = 250 V, V_{GS} = 0 V$ $V_{DS} = 200 V, T_{C} = 125^{\circ}C$				1 10	μΑ μΑ
I _{GSSF}	Gate-Body	/ Leakage Current, Forwar	rd V _{GS} =	= 30 V, V _{DS} = 0 V				100	nA
I _{GSSR}	Gate-Body	/ Leakage Current, Revers	e V _{GS} =	$V_{GS} = -30 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				-100	nA
On Charac	teristics								
V _{GS(th)}	Gate Thre	shold Voltage	V _{DS} =	V_{GS} , I_D = 250 μ A		3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS} =	= 10 V, I _D = 2.2 A			0.9	1.1	Ω
9 _{FS}	Forward T	ransconductance	V _{DS} =	40 V, I _D = 2.2 A			5.5		S
Dynamic C	haracterist	ics							
C _{iss}	Input Capa	acitance		V _{DS} = 25 V, V _{GS} = 0 V,			194	250	pF
C _{oss}	Output Ca	pacitance	f = 1 N	f = 1 MHz			38	50	pF
C _{rss}	Reverse T	verse Transfer Capacitance					5	8	pF
Switching	Characteris	stics							
t _{d(on)}	Turn-On D	elay Time		= 125 V, I _D = 6 A,			10	30	ns
t _r	Turn-On R	lise Time	V _{GS} =	V_{GS} = 10 V, R_{G} = 25 Ω			25	60	ns
t _{d(off)}	Turn-Off D	elay Time					7	24	ns
t _f	Turn-Off F	all Time			(Note 4)		12	34	ns
Qg	Total Gate	Charge	V _{DS} =	$V_{DS} = 200 \text{ V}, \text{ I}_{D} = 6 \text{ A},$ $V_{GS} = 10 \text{ V}$ (Note 4)			4.5	6	nC
Q _{gs}	Gate-Sour	ce Charge	V _{GS} =				1.5		nC
Q _{gd}	Gate-Drair	n Charge					1.8		nC
Drain-Sou	rce Diode C	haracteristics and Maxir	num Rating	gs					
I _S	I _S Maximum Continuous Drain-Source Dio		Diode Forw	ard Current				4.4	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F		e Forward	Forward Current				18	Α
V _{SD}	Drain-Sou	rce Diode Forward Voltage	e V _{GS} =	0 V, I _S = 4.4 A,				1.4	V
t _{rr}	Reverse R	ecovery Time	V _{GS} =	= 0 V, I _S = 6 A			145		ns
Q _{rr}	Reverse R	ecovery Charge		=100 A/μs			0.55		μC

Notes:

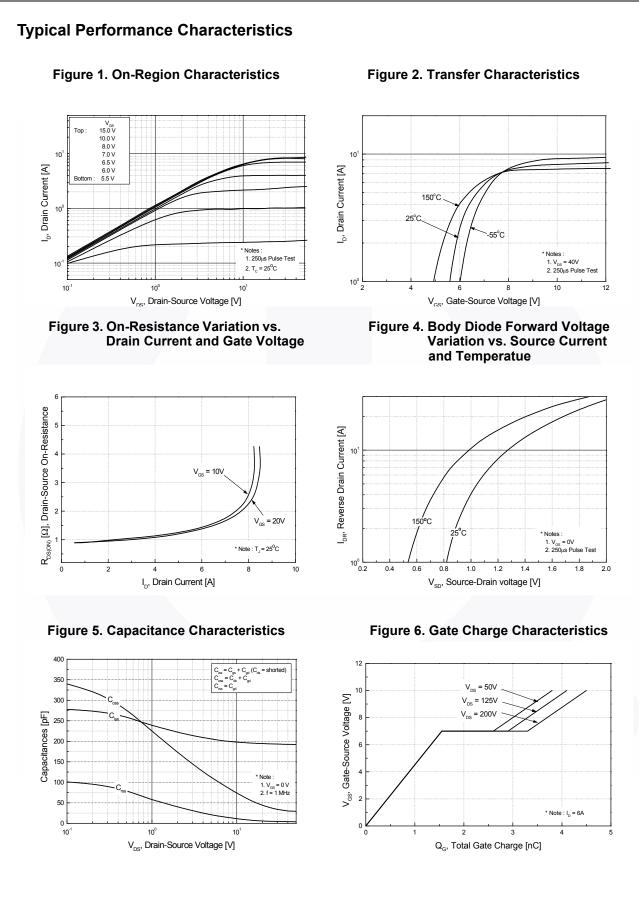
1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. L = 1.2 mH, I_{AS} = 4.4 A, V_{DD} = 50 V, R_G = 25 $\Omega,$ starting T_J = 25°C.

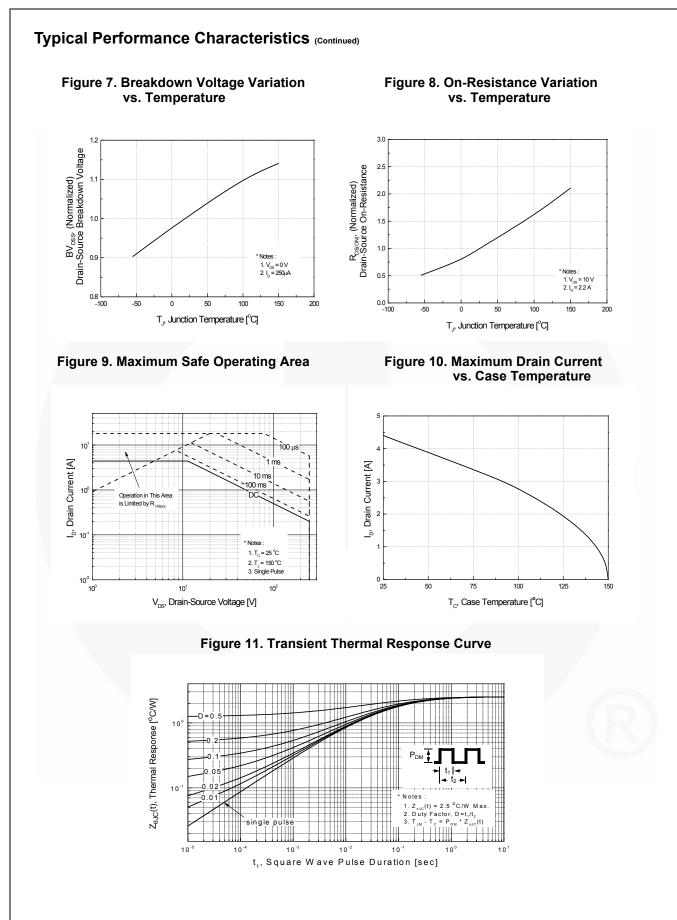
3. I_{SD} \leq 4.4 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C.

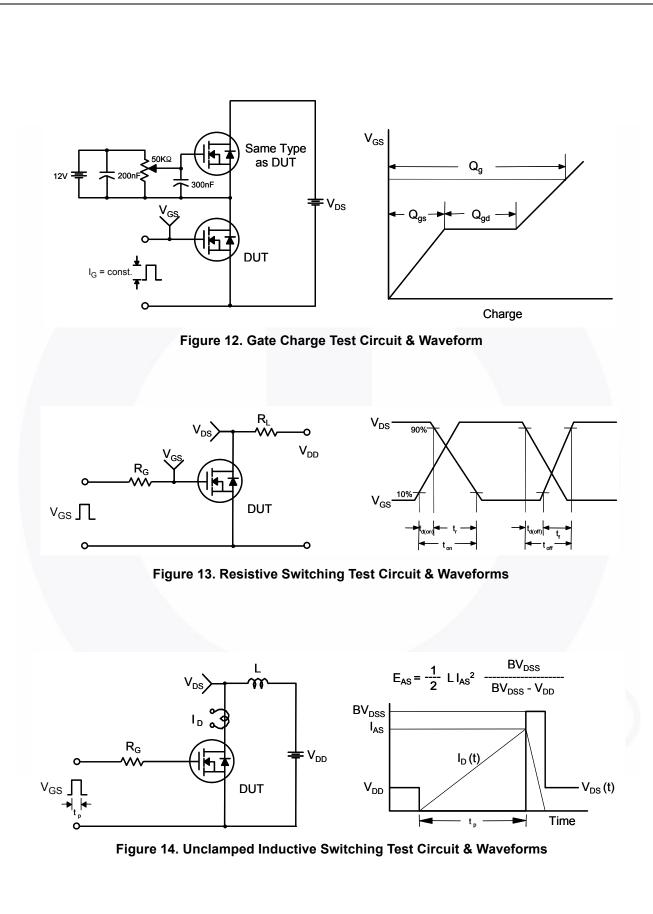
4. Essentially Independent of Operating Temperature Typical Characteristics

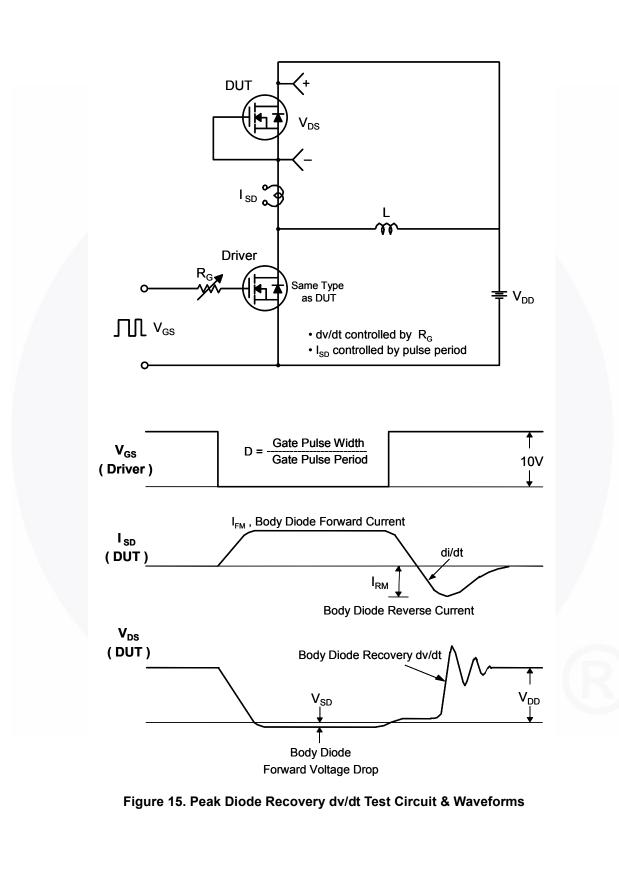
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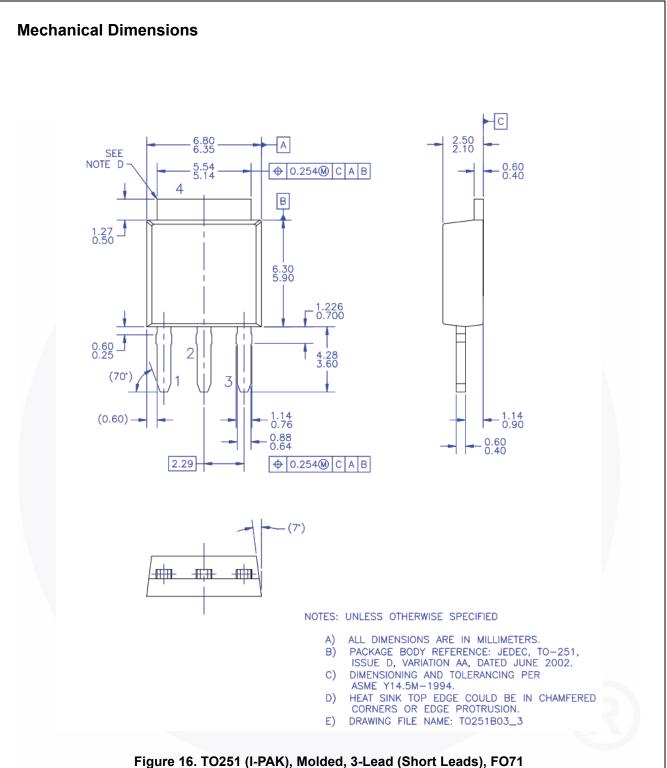


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